NVMTS0D6N04CL

MOSFET – Power, Single N-Channel

40 V, 0.42 mΩ, 554.5 A

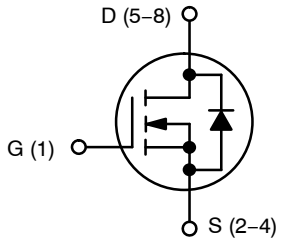
Features

- Small Footprint (8x8 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- Wettable Flank Plated for Enhanced Optical Inspection
- AEC−101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

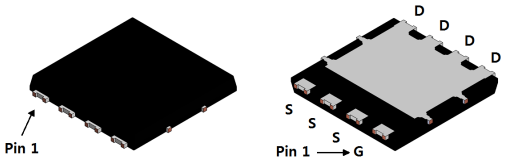
ON Semiconductor®

www.onsemi.com

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
40 V	0.42 mΩ @ 10 V	554.5 A
	0.66 mΩ @ 4.5 V	



N−CHANNEL MOSFET



POWER 88
CASE 507AP

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	40	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{\theta JC}$ (Note 2)	Steady State	T_C = 25°C	I_D	554.5	A
		T_C = 100°C		392.1	
Power Dissipation $R_{\theta JC}$ (Note 2)	Steady State	T_C = 25°C	P_D	245.4	W
		T_C = 100°C		122.7	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	T_A = 25°C	I_D	78.9	A
		T_A = 100°C		55.8	
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	Steady State	T_A = 25°C	P_D	5.0	W
		T_A = 100°C		2.5	
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	900	A
Operating Junction and Storage Temperature Range			T_J, T_{stg}	−55 to +175	°C
Source Current (Body Diode)			I_S	204.5	A
Single Pulse Drain−to−Source Avalanche Energy ($I_{L(pk)}$ = 52.7 A)			E_{AS}	2058	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

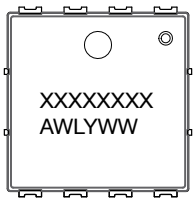
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case − Steady State (Note 2)	$R_{\theta JC}$	0.61	°C/W
Junction−to−Ambient − Steady State (Note 2)	$R_{\theta JA}$	30.2	

1. Surface−mounted on FR4 board using a 1 in^2 pad size, 1 oz. Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

MARKING DIAGRAM



XXX = Device Code
(8 A−N characters max)
A = Assembly Location
WL = 2−digit Wafer Lot Code
Y = Year Code
WW = Work Week Code

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		40			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I_D = 250 μA, ref to 25°C			12.6		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 40 V	T_J = 25°C			10	μA
			T_J = 125°C			250	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V				100	nA
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.2		2.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	I_D = 250 μA, ref to 25°C			−6.0		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 50 A		0.35	0.42	mΩ
		V_{GS} = 4.5 V	I_D = 50 A		0.52	0.66	
Forward Transconductance	g_{FS}	V_{DS} =5 V, I_D = 50 A			323		S
Gate Resistance	R_G	T_A = 25°C			1.0		Ω
CHARGES, CAPACITANCES & GATE RESISTANCE							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 20 V			16013		pF
Output Capacitance	C_{OSS}				6801		
Reverse Transfer Capacitance	C_{RSS}				299		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 20 V; I_D = 50 A			126		nC
Threshold Gate Charge	$Q_{G(TH)}$				22.5		
Gate−to−Source Charge	Q_{GS}				39.9		
Gate−to−Drain Charge	Q_{GD}				38.4		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 20 V; I_D = 50 A			265		nC
SWITCHING CHARACTERISTICS, V_{GS} = 4.5 V (Note 4)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 4.5 V, V_{DS} = 20 V, I_D = 50 A, R_G = 6 Ω			89.4		ns
Rise Time	t_r				111		
Turn−Off Delay Time	$t_{d(OFF)}$				180		
Fall Time	t_f				84.7		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 50 A	T_J = 25°C		0.75	1.2	V
			T_J = 125°C		0.6		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dIS/dt = 100 A/μs, I_S = 50 A			99.3		ns
Charge Time	t_a				62.4		
Discharge Time	t_b				36.9		
Reverse Recovery Charge	Q_{RR}				228		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
4. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

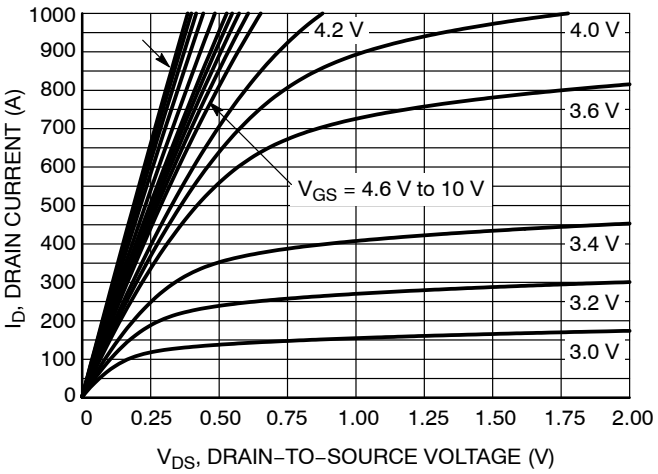


Figure 1. On−Region Characteristics

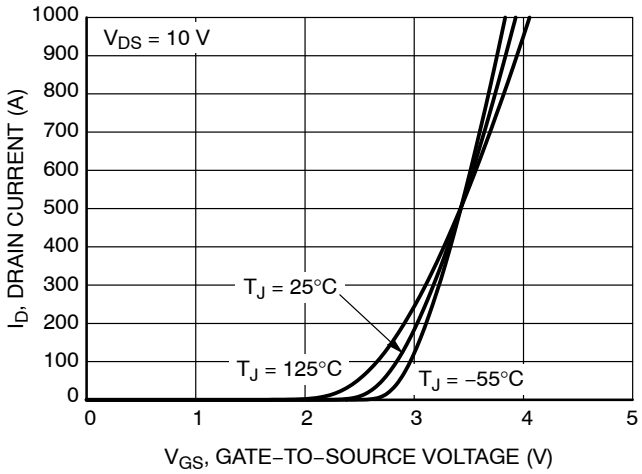


Figure 2. Transfer Characteristics

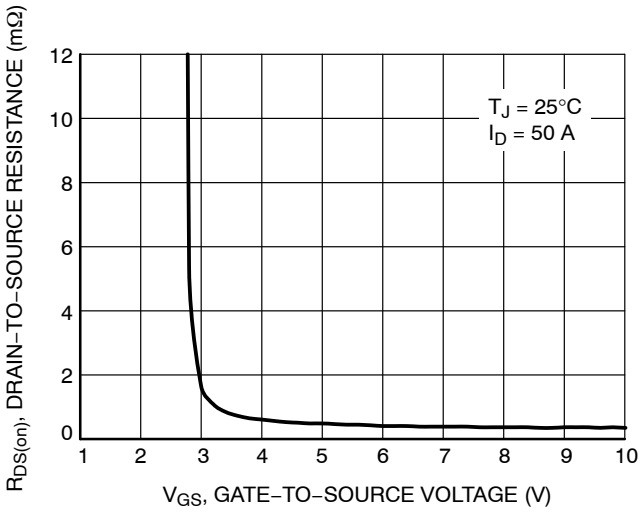


Figure 3. On−Resistance vs. Gate−to−Source Voltage

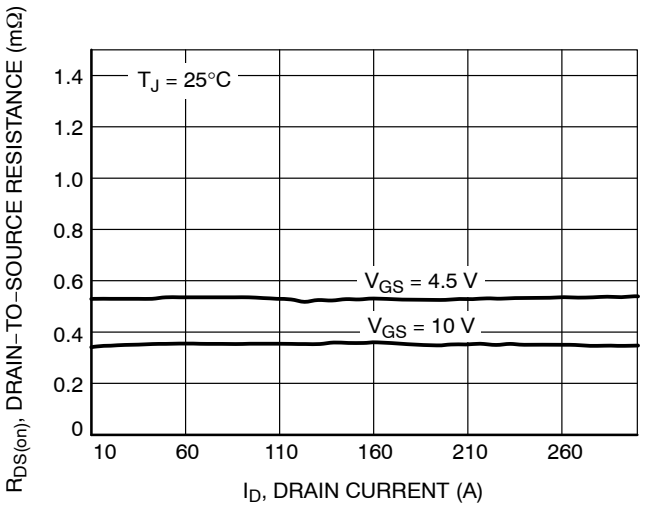


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

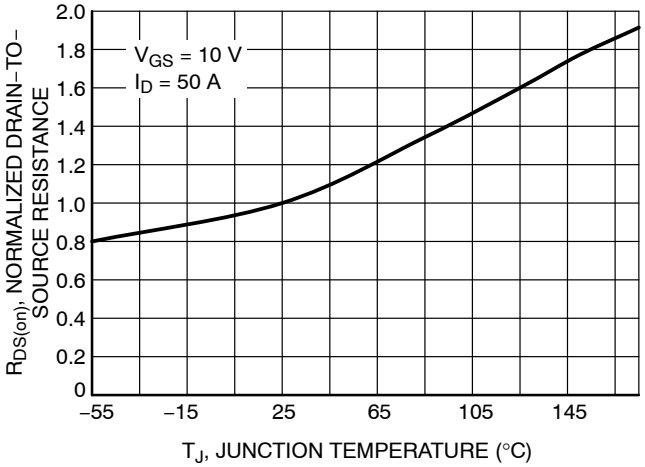


Figure 5. On−Resistance Variation with Temperature

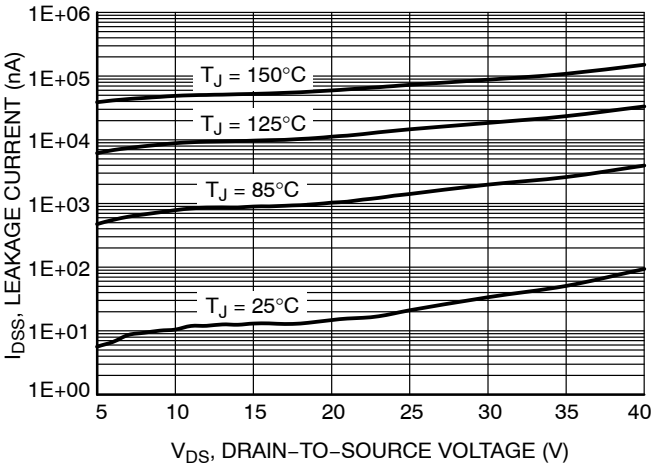


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

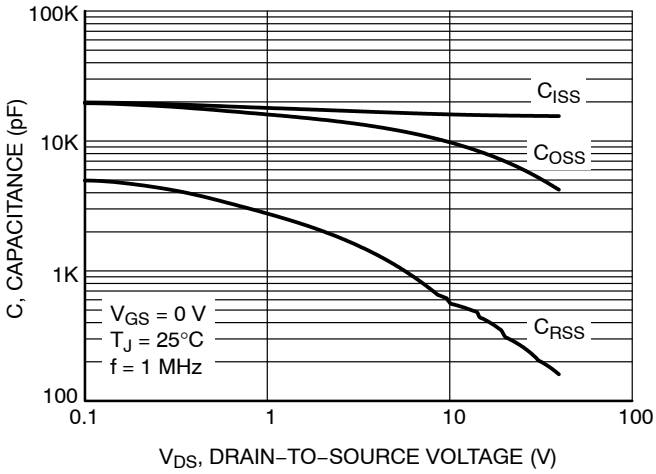


Figure 7. Capacitance Variation

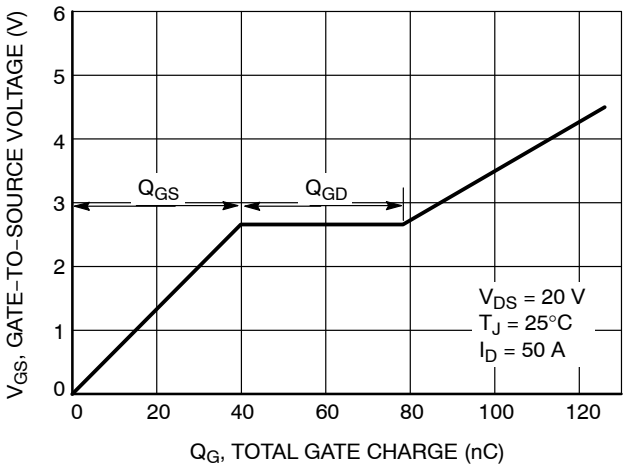


Figure 8. Gate−to−Source Voltage vs. Total Charge

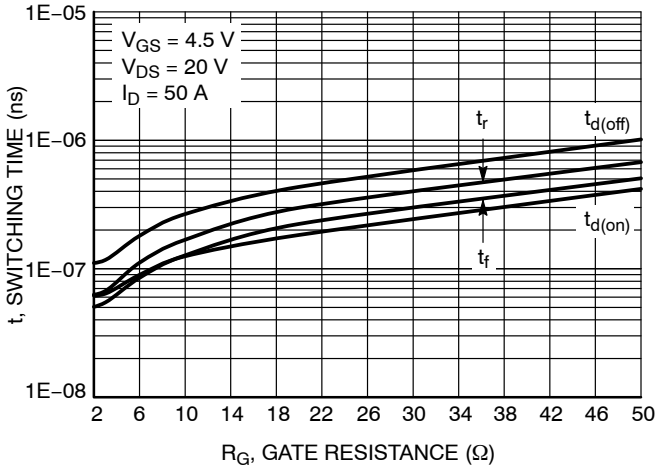


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

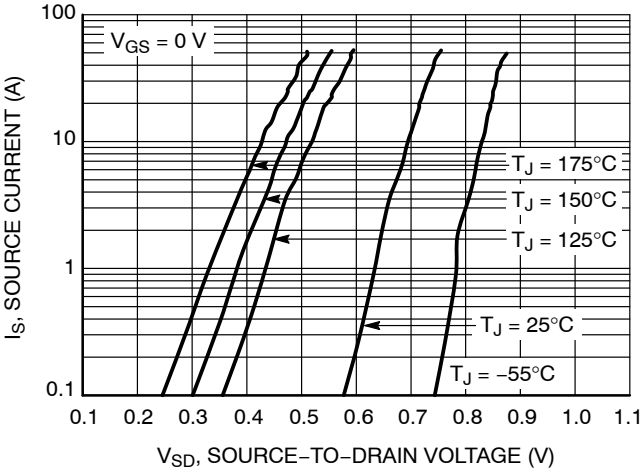


Figure 10. Diode Forward Voltage vs. Current

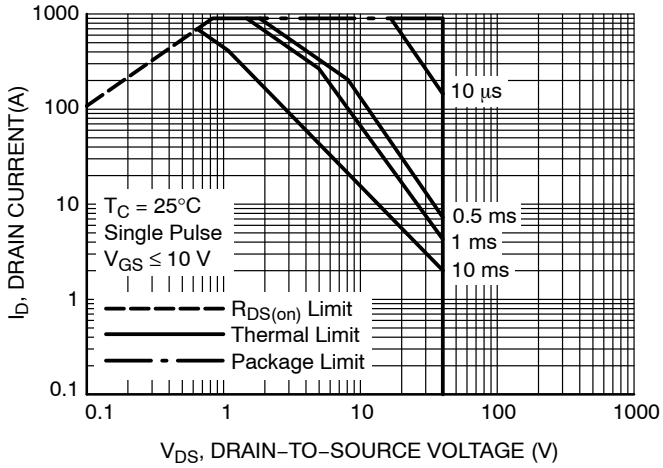


Figure 11. Maximum Rated Forward Biased Safe Operating Area

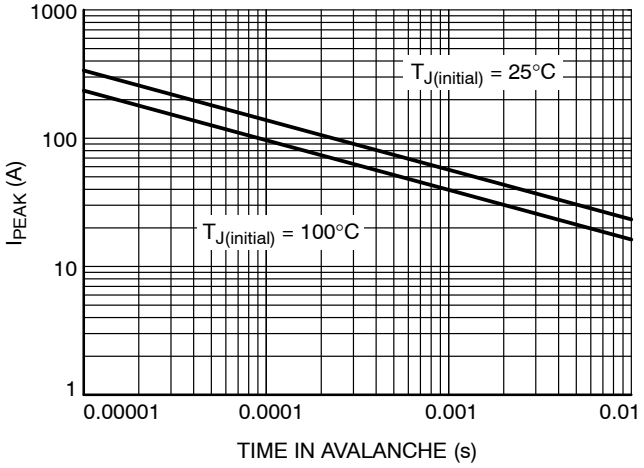


Figure 12. I_{PEAK} vs. Time in Avalanche

TYPICAL CHARACTERISTICS

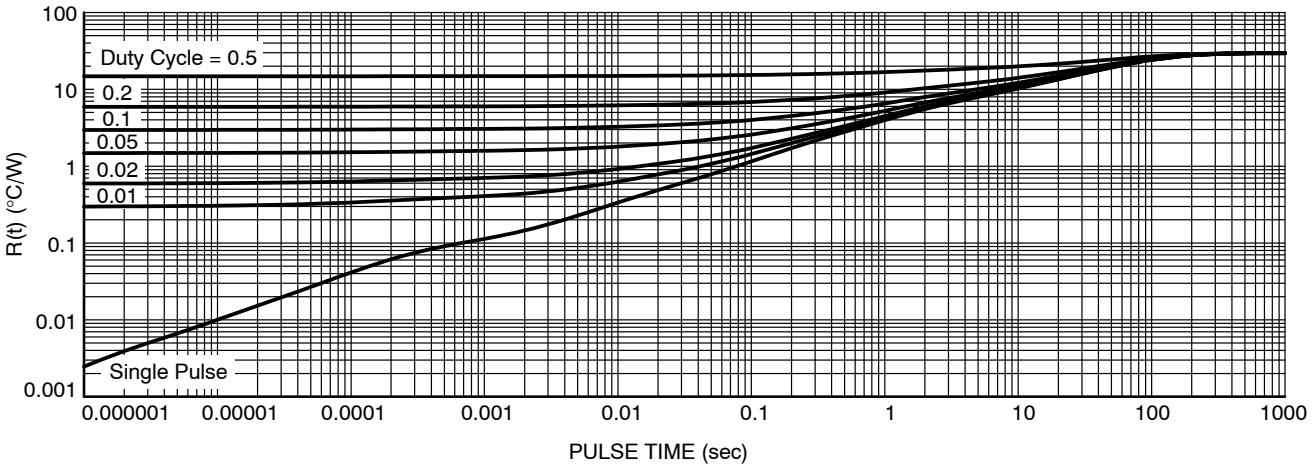
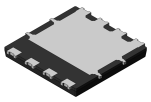


Figure 13. Thermal Characteristics

DEVICE ORDERING INFORMATION

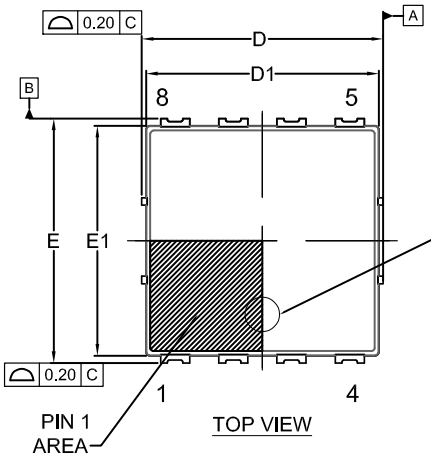
Device	Marking	Package	Shipping†
NVMTS0D6N04CLTXG	0D6N04CL	POWER 88 (Pb−Free)	3000 / Tape & Reel

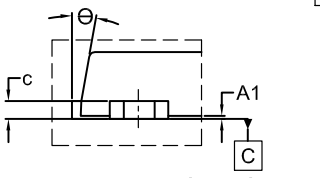
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



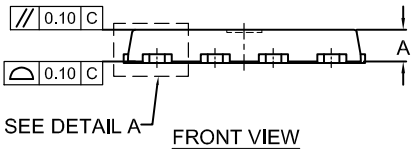
TDFNW8 8.30x8.40x1.10, 2.00P
CASE 507AP
ISSUE E

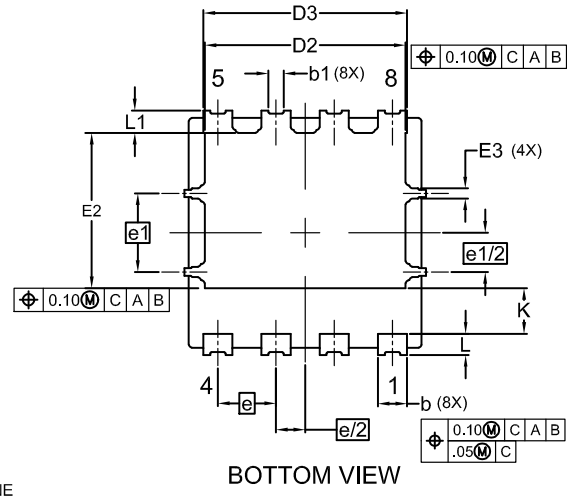
DATE 08 MAY 2024





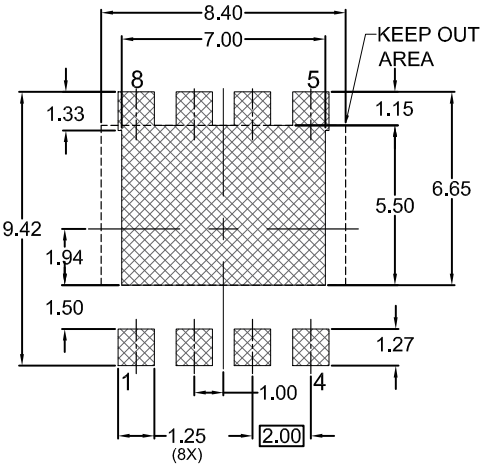
DETAIL A
SCALE: 2X



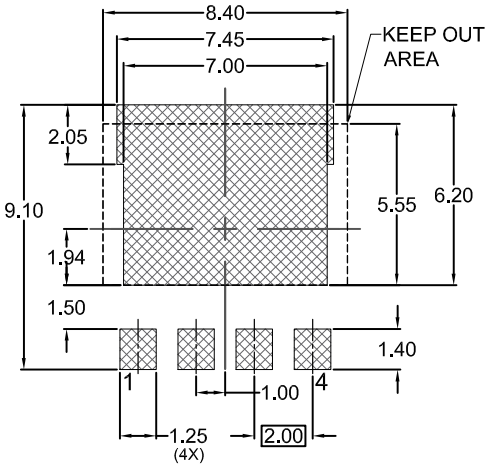


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



RECOMMENDED LAND PATTERN*



UNIVERSAL LAND PATTERN*

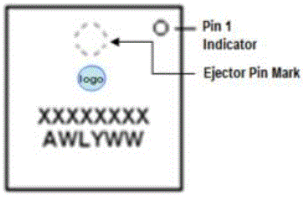
*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	1.00	1.10	1.20
A1	0.00	---	0.05
b	0.90	1.00	1.10
b1	0.35	0.45	0.55
c	0.23	0.28	0.33
D	8.20	8.30	8.40
D1	7.90	8.00	8.10
D2	6.80	6.90	7.00
D3	6.90	7.00	7.10
E	8.30	8.40	8.50
E1	7.80	7.90	8.00
E2	5.24	5.34	5.44
E3	0.25	0.35	0.45
e	2.00 BSC		
e/2	1.00 BSC		
e1	2.70 BSC		
e1/2	1.35 BSC		
K	1.50	1.57	1.70
L	0.64	0.74	0.84
L1	0.67	0.77	0.87
Θ	0°	---	12°

TDFNW8 8.30x8.40x1.10, 2.00P
CASE 507AP
ISSUE E

DATE 08 MAY 2024

GENERIC
MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot Code
Y = Year Code
WW = Work Week Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	**98AON80534G**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**TDFNW8 8.30x8.40x1.10, 2.00P**		**PAGE 2 OF 2**

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales